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# The growth of interfacial compounds between titanium dioxide and bismuth oxide

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#### Abstract

The growth of interfacial compounds between  $TiO_2$  and  $Bi_2O_3$  during transient liquid phase bonding at 900, 1000 and 1100 °C for various times was investigated. The microstructures and compositions of compounds in joints were analyzed by means of SEM and EPMA. It was found that the compound  $Bi_4Ti_3O_{12}$  forms initially and replaces the  $Bi_2O_3$  interlayer.  $Bi_2Ti_4O_{11}$  then arises at the interface between  $Bi_4Ti_3O_{12}$  and  $TiO_2$  and the metastable  $Bi_2Ti_2O_7$  phase appears last at the interface between  $Bi_4Ti_3O_{12}$  and  $Bi_2Ti_4O_{11}$ . The modes and activation energies of the growth of  $Bi_4Ti_3O_{12}$  and  $Bi_2Ti_4O_{11}$  were determined respectively. Holes in the middle of the joint heated at 1100 °C for 24 h were also found. © 2009 Elsevier Ltd and Techna Group S.r.l. All rights reserved.

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### 1. Introduction

The joining of industrial ceramic has been considered as a high-cost and time-consuming task. There are mainly two different ways: diffusion bonding and brazing. Ceramics joined by diffusion bonding usually has excellent strength and toughness; however, it takes a lot of time and energy. For example, the joining of alumina by diffusion bonding has been carried out at 1500 °C under a uniaxial pressure of 138 MPa and a post 3 h heat treatment at 1875 °C [1]. Comparably, brazing, especially active brazing, has a lower operating temperature and even needs no loading [2]. Despite these advantages, low melting metallic brazes limit the usage temperature of joint.

Transient liquid phase bonding, also named as isothermal solidification and diffusion brazing for joining at above 450 °C, facilitates the usage temperatures of joint to go above the joining temperature [3–6]. The trick of that is the total consumption of brazes and the simultaneous formation of high melting compounds between matrixes and brazes. This technique has been well proven applicable in joining some metallic and ceramic parts. Most brazes used are composed of

Recently, Chang and Huang published research on joining alumina (Al<sub>2</sub>O<sub>3</sub>) via a boron oxide (B<sub>2</sub>O<sub>3</sub>) interlayer and a joining strength above 150 MPa was achieved [7]. The success of joining Al<sub>2</sub>O<sub>3</sub> via a B<sub>2</sub>O<sub>3</sub> interlayer relies on the low eutectic temperature and on the presence of high melting compounds in the Al<sub>2</sub>O<sub>3</sub>-B<sub>2</sub>O<sub>3</sub> phase diagram. Only a few binary ceramic systems possess a eutectic point below 1000 °C and a proper compound. Among them, the titanium dioxide (TiO<sub>2</sub>) and bismuth oxide (Bi<sub>2</sub>O<sub>3</sub>) binary system is an ideal candidate system whose eutectic temperature is 835 °C and compounds melt at over 1200 °C. This data can be seen in Fig. 1, the Bi<sub>2</sub>O<sub>3</sub>– TiO<sub>2</sub> phase diagram [8]. TiO<sub>2</sub> is widely used as a catalyst in photoelectrochemical applications [9]; contrarily, little research has been done on the joining of TiO<sub>2</sub> [10]. In this paper, a study on the compound formation during the joining of TiO<sub>2</sub> bulk phases via a Bi<sub>2</sub>O<sub>3</sub> interlayer by the transient liquid phase bonding technique is reported.

# 2. Experimental

99.9%  $TiO_2$  powder (SHOWA, 2021-7760) and 99.9%  $Bi_2O_3$  powder (ACROS, A102277101) were the raw materials.

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metallic ingredients. Although the intermetallic compounds possess high melting points and high strength, their distinct electronic properties from ceramic bulk phases may lure corrosive aggression.

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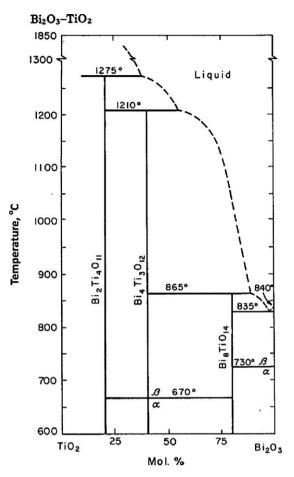


Fig. 1. Bi<sub>2</sub>O<sub>3</sub>-TiO<sub>2</sub> phase diagram [8].

Aqueous  ${\rm TiO_2}$  slurry with 50 wt. % solid content and 4 wt. % dispersant was prepared. The dispersant was Darvon 7.  ${\rm TiO_2}$  green cakes were formed by pressure slip casting of the slurry and then sintered at 1350 °C after dehydration at 40 and 60 °C for 1 day each, and de-dispersant at 200 °C for 6 h. The sintered bulks were cut into 2 cm  $\times$  1.5 cm  $\times$  1 cm pieces and polished. The density and crystal structures were measured by Archimedes' method and X-ray diffraction (XRD, MAC Science MXP3).

The  $Bi_2O_3$  powder was mixed with a little water to get the ceramic paste. The paste was spread over one large side of the  $TiO_2$  bulk with a 0.1 mm spacing blade process to form a  $Bi_2O_3$  interlayer. An uncoated  $TiO_2$  bulk was then put on the covered side of the  $TiO_2$  bulk and a  $TiO_2$ – $Bi_2O_3$ – $TiO_2$  sandwich was prepared. The sandwich samples were fastened with stainless steel wire and put into an electric furnace (Thermolyne, 1100). A small load of 1 kPa was applied on the samples to control the interlayer thickness at about 20  $\mu$ m. The samples were prejoined at 850 °C for 1.5 h. Then they were heated to three different temperatures (900, 1000, 1100 °C) and held for various times (0.5–72 h). Fig. 2 represents the schema of the materials evolution during the joining process.

The joined samples were cut, mounted, ground and polished in sequence. We observed the microstructure of the joint cross-section by scanning electron microscopy (SEM, JEOL JSM-5400) and analyzed the composition of the interface by electron

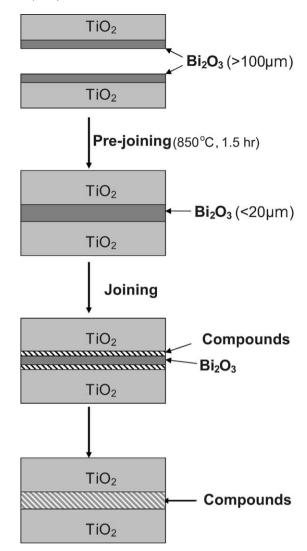


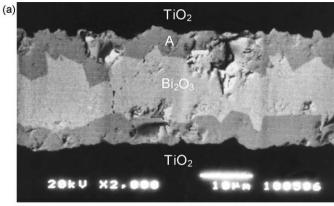
Fig. 2. Schema of materials evolution during the joining process.

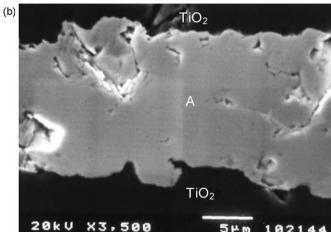
probe microanalysis (EPMA, JEOL 8900R). The samples were also fractured to reveal the interlayer and the fractured surface was analyzed by XRD. The crystal structure and composition, respectively determined from XRD and EPMA, were mutually verified.

# 3. Results and discussion

# 3.1. Compound formation in joints at various temperatures

The density of the  $TiO_2$  bulk was  $4.16~g/cm^3$  (relative density: 98.3%). It is yellowish brown and has a rutile structure. Fig. 3 shows the SEM micrographs of the joint cross-sections in the samples heated at  $900~^{\circ}C$  for 0.5–24~h, where the dark area is  $TiO_2$  and the cross-light area is the interlayer. Though polished, the sample surface is still scraggy due to the fragility of  $Bi_2O_3$ . After heated for 1 h, a 5  $\mu$ m thick, light grey layer, labeled "A", arises at the  $B_2O_3$ – $TiO_2$  interface (Fig. 3a). The thickness of this layer increases with increased heating time. The light grey layer replaces the whole  $Bi_2O_3$  interlayer after a 3 h heat treatment at  $900~^{\circ}C$  (Fig. 3b). The Ti/Bi ratio of the





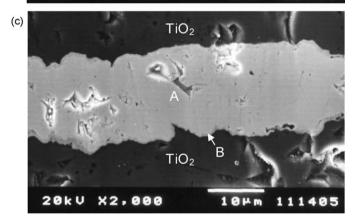


Fig. 3. SEM micrographs of the joint cross-sections heated at 900  $^{\circ}$ C for (a) 1 h, (b) 3 h and (c) 6 h.

compound A measured by EPMA is about 3/4 which corresponds to the  $Bi_4Ti_3O_{12}$  compound. The XRD pattern of the fractured surface of this sample (Fig. 4) verifies that the compound A is  $Bi_4Ti_3O_{12}$ . The JCPDS (Joint Committee on Powder Diffraction Standards) spectrum of  $Bi_4Ti_3O_{12}$  is also given at the bottom of Fig. 4 for comparison.

A darker compound (B) appears at the interface between  $TiO_2$  and  $Bi_4Ti_3O_{12}$  arising when the sample is heat treated for 6 h (Fig. 3c); its thickness is 0.5  $\mu$ m and becomes thicker as heating goes on. It reaches 1.7  $\mu$ m after a one-day long heat treatment at 900 °C. This compound B is  $Bi_2Ti_4O_{11}$  according to the Bi/Ti = 2 from EPMA. The thicknesses of the interfacial

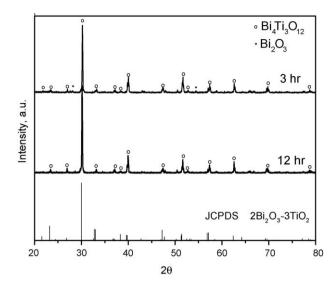


Fig. 4. XRD pattern of the fractured surface of the joint heated at 900  $^{\circ}$ C for 3 h.

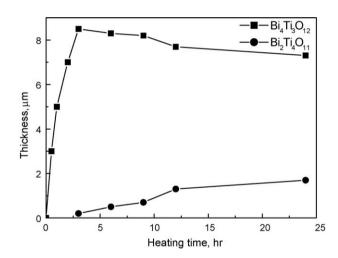
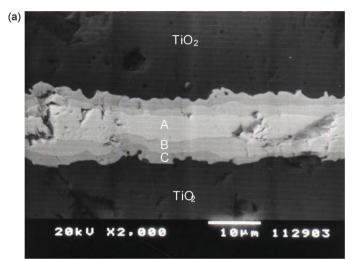


Fig. 5. Thickness of compounds in the joint region heated at 900  $^{\circ}\text{C}$  for various times.

compounds,  $Bi_4Ti_3O_{12}$  and  $Bi_2Ti_4O_{11}$ , for various heating times are plotted in Fig. 5.

Heat treatments at 1000 °C for various times result in the formation of a three-layer structure of interfacial compounds. The SEM micrograph of the joint cross-section in the sample heated for 48 h is shown in Fig. 6a, for example. The three compounds are A:  $Bi_4Ti_3O_{12}$ , B:  $Bi_2Ti_2O_7$  and C:  $Bi_2Ti_4O_{11}$  as clearly indicated in Fig. 6b. It must be mentioned that the  $Bi_2Ti_2O_7$  compound is in a metastable phase.

The thicknesses of these compounds are plotted in Fig. 7 as a function of heating time.  $Bi_4Ti_3O_{12}$  initially forms and takes up the whole interlayer quite fast. Just after 0.5 h heating, no  $Bi_2O_3$  is observed.  $Bi_2Ti_4O_{11}$  arises at the interface between  $TiO_2$  and  $Bi_4Ti_3O_{12}$ . It grows until the appearance of  $Bi_2Ti_2O_7$ .  $Bi_2Ti_2O_7$  appears suddenly with a thickness of 2.5  $\mu$ m in the sample heated for 6 h, and in the meantime  $Bi_2Ti_4O_{11}$  tends to disappear abruptly. Thereafter both  $Bi_2Ti_2O_7$  and  $Bi_2Ti_4O_{11}$  grow steadily. The thickest  $Bi_2Ti_2O_7$  is observed in the sample heated at 1000 °C for 24 h, while  $Bi_4Ti_3O_{12}$  reaches its



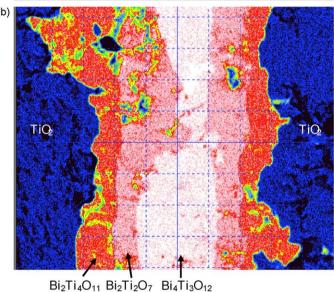


Fig. 6. Joint cross-section in the sample heated for 48 h: (a) the SEM micrograph and (b) chemical mapping from EPMA.

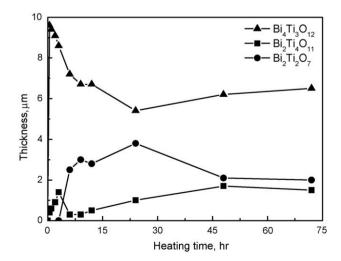


Fig. 7. Thickness of compounds in the joint region heated at 1000  $^{\circ}\mathrm{C}$  for various times.

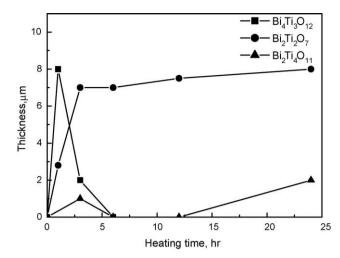


Fig. 8. Thickness of compounds in the joint region heated at 1100 °C for various times

maximum thickness. After a 48 h or longer heat treatment, the thicknesses of these three compounds do not change any more.

Fig. 8 represents the thickness of compounds vs. heating time diagram at 1100 °C. As the joining temperature increases close to the incongruent melting point 1210 °C of  $Bi_4Ti_3O_{12}$ ,  $Bi_4Ti_3O_{12}$  appears and vanishes from the interlayer within 6 h. After that, the metastable  $Bi_2Ti_2O_7$  phase is the dominant one.  $Bi_2Ti_4O_{11}$  is found in the 3 h sample, but in samples heated for longer times it remains undetectable until the sample is heated for 24 h.

Fig. 9 shows the SEM micrograph of the joint cross-section heated at  $1100\,^{\circ}\text{C}$  for 24 h. As mentioned previously, the dominant light grey phase (A) is  $\text{Bi}_2\text{Ti}_2\text{O}_7$  and the darker stripe (B) at its fringes is  $\text{Bi}_2\text{Ti}_4\text{O}_{11}$ . The holes in the middle of the interlayer ( $\text{Bi}_2\text{Ti}_2\text{O}_7$ ) may result from the formation of the stable  $\text{Bi}_2\text{Ti}_4\text{O}_{11}$  phase. The diffusion of Bi atoms from  $\text{Bi}_2\text{Ti}_2\text{O}_7$  (source) toward the  $\text{Bi}_2\text{Ti}_4\text{O}_{11}$  (sink) leaves vacancies behind. The holes are the aggregations of these vacancies which are quite mobile at this elevated temperature. The holes may give rise to a severe embrittlement of the joint.

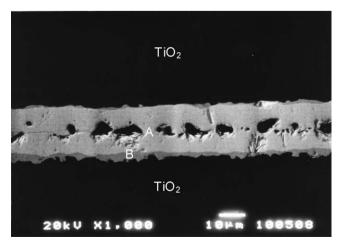


Fig. 9. SEM micrograph of the joint cross-section heated at 1100 °C for 24 h.

#### 3.2. Activation energy of compound formation

The equation  $x = (Kt)^n$  is the typical equation to describe the growth kinetics of an interfacial compound, where x is the compound thickness, K is the growth constant, t is time and n is the characteristic growth exponent. In the case of a diffusion-controlled growth, n = 0.5. If n = 1, the interfacial reaction is the dominant path for growth. Fig. 10 represents three thickness-time diagrams in a log scale for Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>, Bi<sub>2</sub>Ti<sub>4</sub>O<sub>11</sub> and Bi<sub>2</sub>Ti<sub>2</sub>O<sub>7</sub>, respectively. The data for compound thickness in

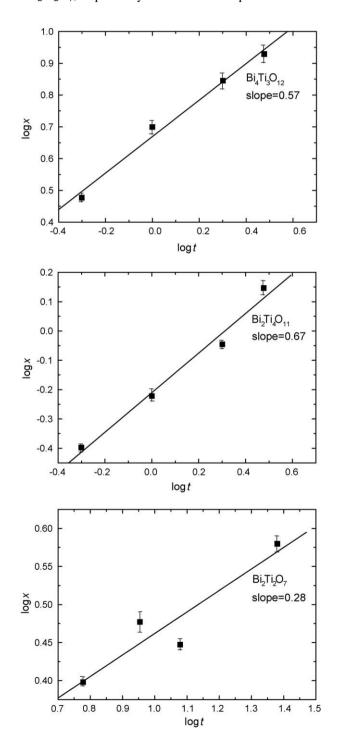


Fig. 10. Thickness-time diagrams in a log scale for three compounds.

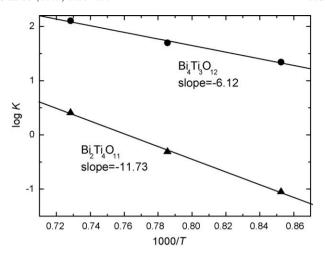


Fig. 11. log K-1000/T diagram for two compounds.

a three-layer growth was not taken into consideration. The corresponding slopes are 0.57, 0.68 and 0.28 for these compounds. The fact that the growth of  $Bi_4Ti_3O_{12}$  and  $Bi_2Ti_4O_{11}$  is apparently diffusion-controlled can be seen, while that of  $Bi_2Ti_2O_7$  is undetermined probably due to the data scattering.

The growth constant K for Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> and Bi<sub>2</sub>Ti<sub>4</sub>O<sub>11</sub> at 900, 1000 and 1100 °C has been calculated, and, according to the Arrhenius relationship, determined the activation energies of growth from the log K-1000/T diagram (Fig. 11) as

$$Q(Bi_4Ti_3O_{12}) = 50 \,\text{kJ/mol}$$

$$Q(Bi_2Ti_4O_{11}) = 98 \text{ kJ/mol}$$

 $Bi_4Ti_3O_{12}$  has lower activation energy of growth and forms first at the interface between  $TiO_2$  and  $Bi_2O_3$ .

## 4. Conclusion

The growth of interfacial compounds between TiO<sub>2</sub> and Bi<sub>2</sub>O<sub>3</sub> during transient liquid phase bonding at various temperatures for various times was investigated in this study. The microstructures and compositions of compounds in joints were analyzed by means of SEM and EPMA. The crystal structures of some compounds were verified by XRD. It can be concluded that in the samples heated at 900, 1000 and 1100 °C, the compound Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> forms initially and replaces the Bi<sub>2</sub>O<sub>3</sub> interlayer. Bi<sub>2</sub>Ti<sub>4</sub>O<sub>11</sub> arises secondly at the interface between Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> and TiO<sub>2</sub> and the metastable Bi<sub>2</sub>Ti<sub>2</sub>O<sub>7</sub> phase appears last at the interface between Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> and Bi<sub>2</sub>Ti<sub>4</sub>O<sub>11</sub>. The growth of Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> and Bi<sub>2</sub>Ti<sub>4</sub>O<sub>11</sub> is diffusion-controlled with activation energies of 50 and 98 kJ/mol, respectively. Holes in the middle of the joint heated at 1100 °C for 24 h were also found. These holes are probably the aggregates of vacancies which may be induced from the diffusion of Bi atoms accompanying the formation of Bi<sub>2</sub>Ti<sub>4</sub>O<sub>11</sub>.

#### Acknowledgement

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